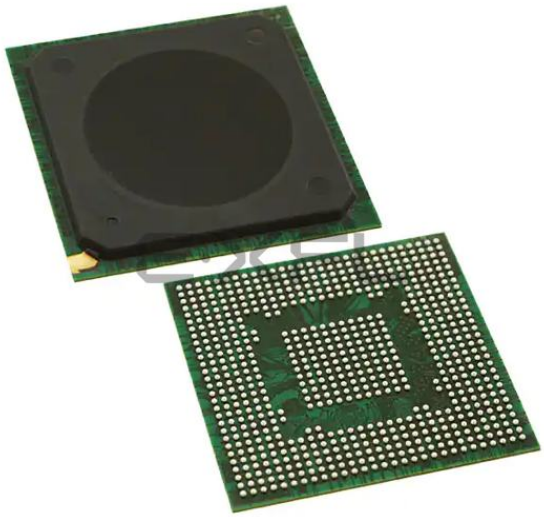

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e300c4s
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	533MHz
Co-Processors/DSP	-
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	SATA 3Gbps (2)
USB	USB 2.0 + PHY (1)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 125°C (TA)
Security Features	-
Package / Case	689-BBGA Exposed Pad
Supplier Device Package	689-TEPBGA II (31x31)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8377vrajf

2.1.3 chipOutput Driver Characteristics

This table provides information on the characteristics of the output driver strengths. The values are preliminary estimates.

Table 4. Output Drive Capability

Driver Type[1]	Output Impedance (Ω)	Supply Voltage
Local bus interface utilities signals	45	LBV_{DD} = 2.5 V, 3.3 V
	40	LBV_{DD} = 1.8 V
PCI signals	25	OV_{DD} = 3.3 V
DDR1 signal	18	GV_{DD} = 2.5 V
DDR2 signal	18	GV_{DD} = 1.8 V
eTSEC 10/100/1000 signals	45	LV_{DD} = 2.5 V, 3.3 V
DUART, system control, I^2C, JTAG, SPI, and USB	45	OV_{DD} = 3.3 V
GPIO signals	45	OV_{DD} = 3.3 V

Note:
1. Specialized SerDes output capabilities are described in the relevant sections of these specifications (such as PCI Express and SATA)

2.2 Power Sequencing

The device requires its power rails to be applied in a specific sequence in order to ensure proper device operation. During the power ramp up, before the power supplies are stable and if the I/O voltages are supplied before the core voltage, there may be a period of time that all input and output pins will actively be driven and cause contention and excessive current. To avoid actively driving the I/O pins and to eliminate excessive current draw, apply the core voltages (V_{DD} and AV_{DD}) before the I/O voltages and assert $\overline{\text{PORESET}}$ before the power supplies fully ramp up. V_{DD} and AV_{DD} must reach 90% of their nominal value before GV_{DD}, LV_{DD}, and OV_{DD} reach 10% of their value, see the following figure. I/O

6.1 DDR1 and DDR2 SDRAM DC Electrical Characteristics

This table provides the recommended operating conditions for the DDR2 SDRAM component(s) of the device when GV_{DD}(typ) = 1.8 V.

Table 13. DDR2 SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 1.8 V

Parameter	Symbol	Min	Max	Unit	Note
I/O supply voltage	GV_{DD}	1.71	1.89	V	1
I/O reference voltage	MV_{REF}	0.49 × GV_{DD}	0.51 × GV_{DD}	V	2, 5
I/O termination voltage	V_{TT}	MV_{REF} – 0.04	MV_{REF} + 0.04	V	3
Input high voltage	V_{IH}	MV_{REF} + 0.140	GV_{DD} + 0.3	V	—
Input low voltage	V_{IL}	–0.3	MV_{REF} – 0.140	V	—
Output leakage current	I_{OZ}	–50	50	μA	4
Output high current (V_{OUT} = 1.40 V)	I_{OH}	–13.4	—	mA	—
Output low current (V_{OUT} = 0.3 V)	I_{OL}	13.4	—	mA	—

Notes:
1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.
2. MV_{REF} is expected to be equal to 0.5 × GV_{DD}, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF}. This rail should track variations in the DC level of MV_{REF}.
4. Output leakage is measured with all outputs disabled, 0 V ≤ V_{OUT} ≤ GV_{DD}.
5. See AN3665, “MPC837xE Design Checklist,” for proper DDR termination.

Table 14 provides the DDR2 capacitance when GV_{DD}(typ) = 1.8 V.

Table 14. DDR2 SDRAM Capacitance for GV_{DD}(typ) = 1.8 V

Parameter	Symbol	Min	Max	Unit	Note
Input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{DIO}	—	0.5	pF	1

Note:
1. This parameter is sampled. GV_{DD} = 1.8 V ± 0.090 V, f = 1 MHz, T_A = 25°C, V_{OUT} = GV_{DD}/2, V_{OUT} (peak-to-peak) = 0.2 V.

This table provides the recommended operating conditions for the DDR SDRAM component(s) when GV_{DD}(typ) = 2.5 V.

Table 15. DDR SDRAM DC Electrical Characteristics for GV_{DD} (typ) = 2.5 V

Parameter	Symbol	Min	Max	Unit	Note
I/O supply voltage	GV_{DD}	2.375	2.625	V	1
I/O reference voltage	MV_{REF}	0.49 × GV_{DD}	0.51 × GV_{DD}	V	2, 5
I/O termination voltage	V_{TT}	MV_{REF} – 0.04	MV_{REF} + 0.04	V	3
Input high voltage	V_{IH}	MV_{REF} + 0.18	GV_{DD} + 0.3	V	—

6.2.2 DDR1 and DDR2 SDRAM Output AC Timing Specifications

This table shows the DDR1 and DDR2 SDRAM output AC timing specifications.

Table 21. DDR1 and DDR2 SDRAM Output AC Timing Specifications

Parameter	Symbol[1]	Min	Max	Unit	Note
MCK*n* cycle time, MCK*n*/$\overline{\text{MCK}n}$ crossing	t_{MCK}	5	10	ns	2
ADDR/CMD output setup with respect to MCK 400 MHz data rate 333 MHz data rate 266 MHz data rate 200 MHz data rate	t_{DDKHAS}	 1.95 2.40 3.15 4.20	 — — — —	ns	3, 7
ADDR/CMD output hold with respect to MCK 400 MHz data rate 333 MHz data rate 266 MHz data rate 200 MHz data rate	t_{DDKHAX}	 1.95 2.40 3.15 4.20	 — — — —	ns	3, 7
$\overline{\text{MCS}n}$ output setup with respect to MCK 400 MHz data rate 333 MHz data rate 266 MHz data rate 200 MHz data rate	t_{DDKHCS}	 1.95 2.40 3.15 4.20	 — — — —	ns	3
$\overline{\text{MCS}n}$ output hold with respect to MCK 400 MHz data rate 333 MHz data rate 266 MHz data rate 200 MHz data rate	t_{DDKHCX}	 1.95 2.40 3.15 4.20	 — — — —	ns	3
MCK to MDQS skew	t_{DDKHMH}	–0.6	0.6	ns	4, 8
MDQ//MDM output setup with respect to MDQS 400 MHz data rate 333 MHz data rate 266 MHz data rate 200 MHz data rate	t_{DDKHDS}, t_{DDKLDS}	 550 800 1100 1200	 — — — —	ps	5, 8
MDQ//MDM output hold with respect to MDQS 400 MHz data rate 333 MHz data rate 266 MHz data rate 200 MHz data rate	t_{DDKHDX}, t_{DDKLDX}	 700 800 1100 1200	 — — — —	ps	5, 8
MDQS preamble start	t_{DDKHMP}	$-0.5 \times t_{MCK} - 0.6$	$-0.5 \times t_{MCK} + 0.6$	ns	6, 8

This figure shows the MII receive AC timing diagram.

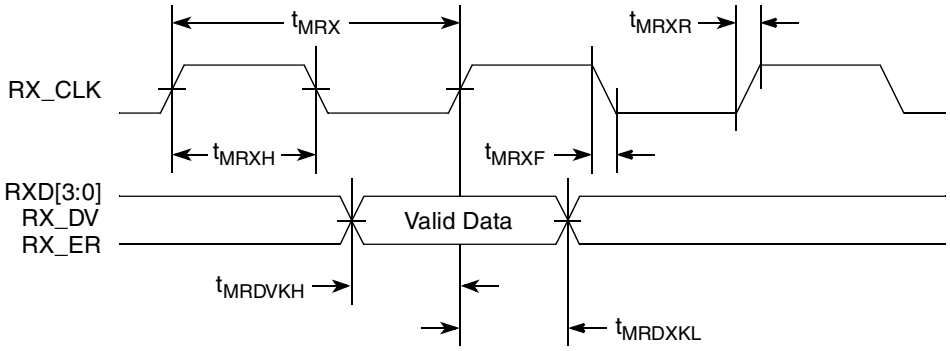

Figure 9. MII Receive AC Timing Diagram

8.2.2 RGMII and RTBI AC Timing Specifications

This table presents the RGMII and RTBI AC timing specifications.

Table 28. RGMII and RTBI AC Timing Specifications

At recommended operating conditions with LV_{DD} of 2.5 V ± 5%.

Parameter	Symbol[1]	Min	Typical	Max	Unit	Note
Data to clock output skew (at transmitter)	t_{SKRGT}	–600	0	600	ps	—
Data to clock input skew (at receiver)	t_{SKRGT}	1.0	—	2.8	ns	2
Clock period	t_{RGT}	7.2	8.0	8.8	ns	3
Duty cycle for 1000Base-T	t_{RGTH}/t_{RGT}	45	50	55	%	4
Duty cycle for 10BASE-T and 100BASE-TX	t_{RGTH}/t_{RGT}	40	50	60	%	3, 4
Rise time (20%–80%)	t_{RGTR}	—	—	0.75	ns	—
Fall time (20%–80%)	t_{RGTF}	—	—	0.75	ns	—
EC_GTX_CLK125 reference clock period	t_{G12}	—	8.0	—	ns	5
EC_GTX_CLK125 reference clock duty cycle measured at $0.5 \times LV_{DD1}$	t_{G125H}/t_{G125}	47	—	53	%	—

Notes:

1. Note that, in general, the clock reference symbol representation for this section is based on the symbols RGT to represent RGMII and RTBI timing. Note also that the notation for rise (R) and fall (F) times follows the clock symbol that is being represented. For symbols representing skews, the subscript is skew (SK) followed by the clock that is being skewed (RGT).
2. This implies that PC board design will require clocks to be routed such that an additional trace delay of greater than 1.5 ns will be added to the associated clock signal.
3. For 10 and 100 Mbps, t_{RGT} scales to 400 ns ± 40 ns and 40 ns ± 4 ns, respectively.
4. Duty cycle may be stretched/shrunk during speed changes or while transitioning to a received packet's clock domains as long as the minimum duty cycle is not violated and stretching occurs for no more than three t_{RGT} of the lowest speed transitioned between
5. This symbol represents the external EC_GTX_CLK125 and does not follow the original signal naming convention.

Table 32. MII Management DC Electrical Characteristics When Powered at 3.3 V

Parameter	Conditions		Symbol	Min	Max	Unit
Supply voltage (3.3 V)	—		LV_{DD1}	3.135	3.465	V
Output high voltage	I_{OH} = –1.0 mA	LV_{DD1} = Min	V_{OH}	2.10	LV_{DD1} + 0.3	V
Output low voltage	I_{OL} = 1.0 mA	LV_{DD1} = Min	V_{OL}	GND	0.50	V
Input high voltage	—		V_{IH}	2.00	—	V
Input low voltage	—		V_{IL}	—	0.80	V
Input high current	LV_{DD1} = Max	V_{IN} [1] = 2.1 V	I_{IH}	—	30	μA
Input low current	LV_{DD1} = Max	V_{IN} = 0.5 V	I_{IL}	–600	—	μA

8.3.2 MII Management AC Electrical Specifications

This table provides the MII management AC timing specifications.

Table 33. MII Management AC Timing Specifications

Parameter	Symbol[1]	Min	Typical	Max	Unit	Note
MDC frequency	f_{MDC}	—	2.5	—	MHz	2
MDC period	t_{MDC}	80	—	400	ns	—
MDC clock pulse width high	t_{MDCH}	32	—	—	ns	—
MDC to MDIO valid	t_{MDKHDV}	$2 \times (t_{plb\_clk} \times 8)$	—	—	ns	4
MDC to MDIO delay	t_{MDKHDX}	10	—	$2 \times (t_{plb\_clk} \times 8)$	ns	2, 4
MDIO to MDC setup time	t_{MDDVKH}	5	—	—	ns	—
MDIO to MDC hold time	t_{MDDXKH}	0	—	—	ns	—
MDC rise time (20%–80%)	t_{MDCR}	—	—	10	ns	3
MDC fall time (80%–20%)	t_{MDCF}	—	—	10	ns	3

Notes:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MDKHDX} symbolizes management data timing (MD) for the time t_{MDC} from clock reference (K) high (H) until data outputs (D) are invalid (X) or data hold time. Also, t_{MDDVKH} symbolizes management data timing (MD) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MDC} clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. This parameter is dependent on the system clock speed.
3. Guaranteed by design.
4. t_{plb_clk} is the platform (CSB) clock divided according to the SCCR[TSEC1CM].

12.1 JTAG DC Electrical Characteristics

This table provides the DC electrical characteristics for the IEEE 1149.1 (JTAG) interface of the chip.

Table 44. JTAG interface DC Electrical Characteristics

Parameter	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}	—	2.5	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	—	—	±30	μA
Output high voltage	V_{OH}	I_{OH} = –8.0 mA	2.4	—	V
Output low voltage	V_{OL}	I_{OL} = 8.0 mA	—	0.5	V
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V

12.2 JTAG AC Timing Specifications

This section describes the AC electrical specifications for the IEEE 1149.1 (JTAG) interface of the device. This table provides the JTAG AC timing specifications as defined in Figure 33 through Figure 36.

Table 45. JTAG AC Timing Specifications (Independent of CLKIN) [1]

Parameter	Symbol[2]	Min	Max	Unit	Note
JTAG external clock frequency of operation	f_{JTG}	0	33.3	MHz	—
JTAG external clock cycle time	t_{JTG}	30	—	ns	—
JTAG external clock pulse width measured at 1.4 V	t_{JTKHKL}	15	—	ns	—
JTAG external clock rise and fall times	t_{JTGR} & t_{JTGF}	0	2	ns	—
$\overline{TRST}$ assert time	t_{TRST}	25	—	ns	3
Input setup times: Boundary-scan data TMS, TDI	 t_{JTDVKH} t_{JTIVKH}	 4 4	 — —	ns	4
Input hold times: Boundary-scan data TMS, TDI	 t_{JTDXKH} t_{JTIXKH}	 10 10	 — —	ns	4
Valid times: Boundary-scan data TDO	 t_{JTKLDV} t_{JTKLOV}	 2 2	 11 11	ns	—
Output hold times: Boundary-scan data TDO	 t_{JTKLDX} t_{JTKLOX}	 2 2	 — —	ns	—

Table 45. JTAG AC Timing Specifications (Independent of CLKIN) [1] (continued)

Parameter	Symbol[2]	Min	Max	Unit	Note
JTAG external clock to output high impedance: Boundary-scan data TDO	 t_{JTKLDZ} t_{JTKLOZ}	 2 2	 19 9	ns	5

Notes:
1. All outputs are measured from the midpoint voltage of the falling/rising edge of t_{TCLK} to the midpoint of the signal in question. The output timings are measured at the pins. All output timings assume a purely resistive 50 Ω load (see Figure 17). Time-of-flight delays must be added for trace lengths, vias, and connectors in the system.
2. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{JTDVKH} symbolizes JTAG device timing (JT) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{JTG} clock reference (K) going to the high (H) state or setup time. Also, t_{JTDXKH} symbolizes JTAG timing (JT) with respect to the time data input signals (D) went invalid (X) relative to the t_{JTG} clock reference (K) going to the high (H) state. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
3. $\overline{\text{TRST}}$ is an asynchronous level sensitive signal. The setup time is for test purposes only.
4. Non-JTAG signal input timing with respect to t_{TCLK}.
5. Non-JTAG signal output timing with respect to t_{TCLK}.

This figure provides the AC test load for TDO and the boundary-scan outputs of the device.

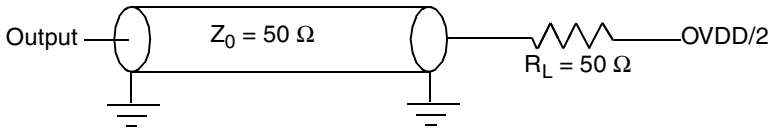

Figure 32. AC Test Load for the JTAG Interface

This figure provides the JTAG clock input timing diagram.

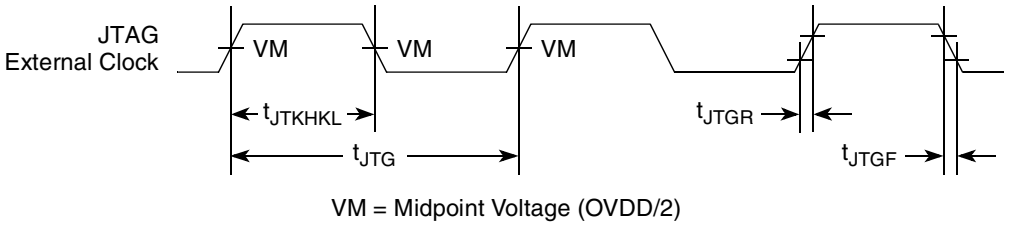

Figure 33. JTAG Clock Input Timing Diagram

This figure provides the $\overline{\text{TRST}}$ timing diagram.

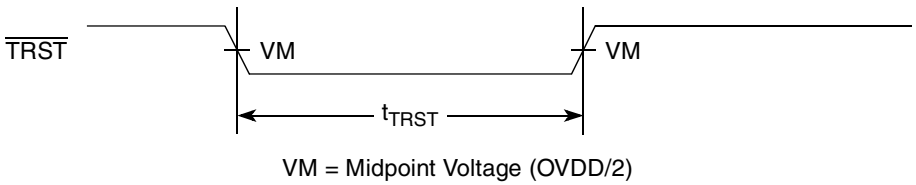

Figure 34. $\overline{\text{TRST}}$ Timing Diagram

Table 53. Differential Receiver (Rx) Input Specifications (continued)

Parameter	Comments	Symbol	Min	Typical	Max	Units	Note
Minimum receiver eye width	The maximum interconnect media and transmitter jitter that can be tolerated by the receiver can be derived as $T_{RX-MAX-JITTER} = 1 - U_{PEEWRX} = 0.6$ UI.	T_{RX-EYE}	0.4	—	—	UI	2, 3
Maximum time between the jitter median and maximum deviation from the median.	Jitter is defined as the measurement variation of the crossing points ($V_{PEDPPRX} = 0$ V) in relation to a recovered Tx UI. A recovered Tx UI is calculated over 3500 consecutive unit intervals of sample data. Jitter is measured using all edges of the 250 consecutive UI in the center of the 3500 UI used for calculating the Tx UI.	$T_{RX-EYE-MEDIAN-to-MAX-JITTER}$	—	—	0.3	UI	2, 3, 7
AC peak common mode input voltage	$V_{PEACPCMRX} = \lvert V_{RXD+} - V_{RXD-}\rvert/2 - V_{RX-CM-DC}$ $V_{RX-CM-DC} = DC_{(avg)}$ of $\lvert V_{RX-D+} - V_{RX-D-}\rvert/2$	$V_{RX-CM-ACp}$	—	—	150	mV	2
Differential return loss	Measured over 50 MHz to 1.25 GHz with the D+ and D– lines biased at +300 mV and –300 mV, respectively.	$RL_{RX-DIFF}$	10	—	—	dB	4
Common mode return loss	Measured over 50 MHz to 1.25 GHz with the D+ and D– lines biased at 0 V.	RL_{RX-CM}	6	—	—	dB	4
DC differential input impedance	RX DC differential mode impedance.	$Z_{RX-DIFF-DC}$	80	100	120	Ω	5
DC Input Impedance	Required RX D+ as well as D- DC impedance (50 ± 20% tolerance).	Z_{RX-DC}	40	50	60	Ω	2, 5
Powered down DC input impedance	Required RX D+ as well as D– DC impedance when the receiver terminations do not have power.	$Z_{RX-HIGH-IMP-DC}$	200 k	—	—	Ω	6
Electrical idle detect threshold	$V_{PEEIDT} = 2 \times \lvert V_{RX-D+} - V_{RX-D-}\rvert$ Measured at the package pins of the receiver	$V_{RX-IDLE-DET-DIFF\ p-p}$	65	—	175	mV	—

Table 53. Differential Receiver (Rx) Input Specifications (continued)

Parameter	Comments	Symbol	Min	Typical	Max	Units	Note
Unexpected Electrical Idle Enter Detect Threshold Integration Time	An unexpected electrical idle (Vrx-diffp-p < Vrx-idle-det-diffp-p) must be recognized no longer than Trx-idle-det-diff-entertime to signal an unexpected idle condition.	$T_{RX-IDLE-DET-DIFF-ENTERTIME}$	—	—	10	ms	—
Total Skew	Skew across all lanes on a link. This includes variation in the length of SKP ordered set (e.g. COM and one to five SKP Symbols) at the Rx as well as any delay differences arising from the interconnect itself.	$L_{RX-SKEW}$	—	—	20	ns	—

Notes:
1. No test load is necessarily associated with this value.
2. Specified at the measurement point and measured over any 250 consecutive UIs. The test load in Figure 44 should be used as the Rx device when taking measurements (also refer to the receiver compliance eye diagram shown in Figure 43). If the clocks to the Rx and Tx are not derived from the same reference clock, the Tx UI recovered from 3500 consecutive UI must be used as a reference for the eye diagram.
3. A T_{Rx-EYE} = 0.40 UI provides for a total sum of 0.60 UI deterministic and random jitter budget for the transmitter and interconnect collected any 250 consecutive UIs. The TRx-EYE-MEDIAN-to-MAX-JITTER specification ensures a jitter distribution in which the median and the maximum deviation from the median is less than half of the total. UI jitter budget collected over any 250 consecutive Tx UIs. It should be noted that the median is not the same as the mean. The jitter median describes the point in time where the number of jitter points on either side is approximately equal as opposed to the averaged time value. If the clocks to the Rx and Tx are not derived from the same reference clock, the Tx UI recovered from 3500 consecutive UI must be used as the reference for the eye diagram.
4. The receiver input impedance will result in a differential return loss greater than or equal to 10 dB with the D+ line biased to 300 mV and the D– line biased to –300 mV and a common mode return loss greater than or equal to 6 dB (no bias required) over a frequency range of 50 MHz to 1.25 GHz. This input impedance requirement applies to all valid input levels. The reference impedance for return loss measurements for is 50 Ω to ground for both the D+ and D– line (that is, as measured by a vector network analyzer with 50-Ω probes, see Figure 44). Note that the series capacitors, C_{Tx}, is optional for the return loss measurement.
5. Impedance during all LTSSM states. When transitioning from a fundamental reset to detect (the initial state of the LTSSM) there is a 5 ms transition time before receiver termination values must be met on all unconfigured lanes of a port.
6. The Rx DC common mode impedance that exists when no power is present or fundamental reset is asserted. This helps ensure that the receiver detect circuit does not falsely assume a receiver is powered on when it is not. This term must be measured at 300 mV above the Rx ground.
7. It is recommended that the recovered Tx UI is calculated using all edges in the 3500 consecutive UI interval with a fit algorithm using a minimization merit function. Least squares and median deviation fits have worked well with experimental and simulated data.

15.5 Receiver Compliance Eye Diagrams

The Rx eye diagram in Figure 43 is specified using the passive compliance/test measurement load (see Figure 44) in place of any real PCI Express Rx component. In general, the minimum receiver eye diagram measured with the compliance/test measurement load (see Figure 44) is larger than the minimum receiver eye diagram measured over a range of systems at the input receiver of any real PCI Express component. The degraded eye diagram at the input receiver is due to traces internal to the package as well as silicon parasitic characteristics that cause the real PCI Express component to vary in impedance from the

18 GPIO

This section describes the DC and AC electrical specifications for the GPIO of the chip.

18.1 GPIO DC Electrical Characteristics

This table provides the DC electrical characteristics for the device GPIO.

Table 65. GPIO DC Electrical Characteristics

This specification applies when operating at 3.3 V ± 165 mV supply.

Parameter	Condition	Symbol	Min	Max	Unit
Output high voltage	I_{OH} = –6.0 mA	V_{OH}	2.4	—	V
Output low voltage	I_{OL} = 6.0 mA	V_{OL}	—	0.5	V
Output low voltage	I_{OL} = 3.2 mA	V_{OL}	—	0.4	V
Input high voltage	—	V_{IH}	2.0	OV_{DD} + 0.3	V
Input low voltage	—	V_{IL}	–0.3	0.8	V
Input current	0 V ≤ V_{IN} ≤ OV_{DD}	I_{IN}	—	± 30	μA

18.2 GPIO AC Timing Specifications

This table provides the GPIO input and output AC timing specifications.

Table 66. GPIO Input AC Timing Specifications

Parameter	Symbol	Min	Unit
GPIO inputs—minimum pulse width	t_{PIWID}	20	ns

Notes:

1. Input specifications are measured from the 50% level of the signal to the 50% level of the rising edge of SYS_CLKIN. Timings are measured at the pin.
2. GPIO inputs and outputs are asynchronous to any visible clock. GPIO outputs should be synchronized before use by any external synchronous logic. GPIO inputs are required to be valid for at least t_{PIWID} ns to ensure proper operation.

This figure provides the AC test load for the GPIO.

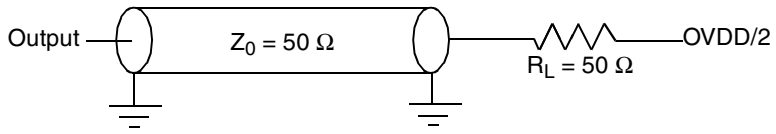

Figure 47. GPIO AC Test Load

19 IPIC

This section describes the DC and AC electrical specifications for the external interrupt pins of the chip.

Table 69. SPI DC Electrical Characteristics (continued)

Parameter	Condition	Symbol	Min	Max	Unit
Output low voltage	I_{OL} = 8.0 mA	V_{OL}	—	0.5	V
Output low voltage	I_{OL} = 3.2 mA	V_{OL}	—	0.4	V

20.2 SPI AC Timing Specifications

This table provides the SPI input and output AC timing specifications.

Table 70. SPI AC Timing Specifications

Parameter	Symbol[1]	Min	Max	Unit
SPI outputs—Master mode (internal clock) delay	t_{NIKHOV}	0.5	6	ns
SPI outputs—Slave mode (external clock) delay	t_{NEKHOV}	2	8	ns
SPI inputs—Master mode (internal clock) input setup time	t_{NIIVKH}	4	—	ns
SPI inputs—Master mode (internal clock) input hold time	t_{NIIXKH}	0	—	ns
SPI inputs—Slave mode (external clock) input setup time	t_{NEIVKH}	4	—	ns
SPI inputs—Slave mode (external clock) input hold time	t_{NEIXKH}	2	—	ns

Notes:
1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state) (reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{NIKHOV} symbolizes the internal timing (NI) for the time SPICLK clock reference (K) goes to the high state (H) until outputs (O) are invalid (X).
2. Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin. The maximum SPICLK input frequency is 66.666 MHz.

This figure provides the AC test load for the SPI.

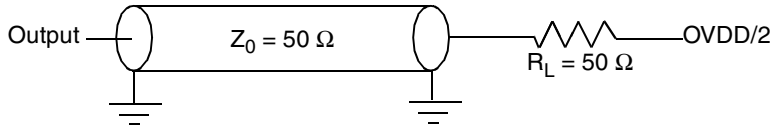

Figure 48. SPI AC Test Load

These figures represent the AC timing from Table 70. Note that although the specifications generally reference the rising edge of the clock, these AC timing diagrams also apply when the falling edge is the active edge.

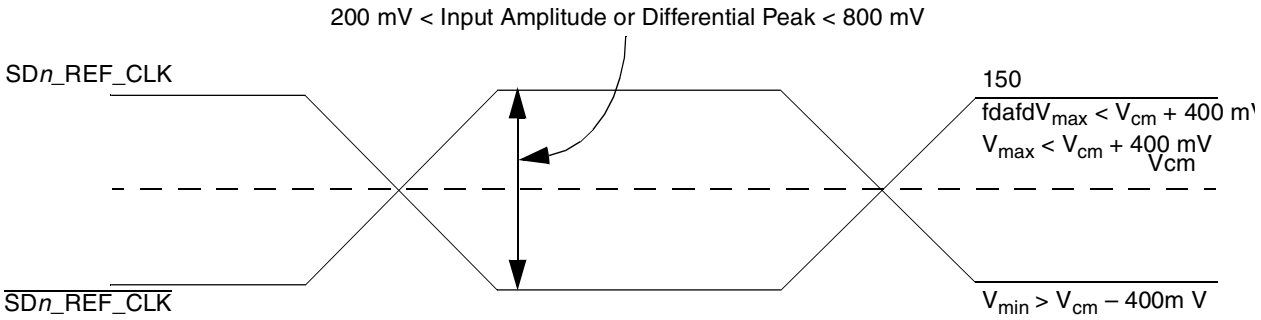

Figure 54. Differential Reference Clock Input DC Requirements (External AC-Coupled)

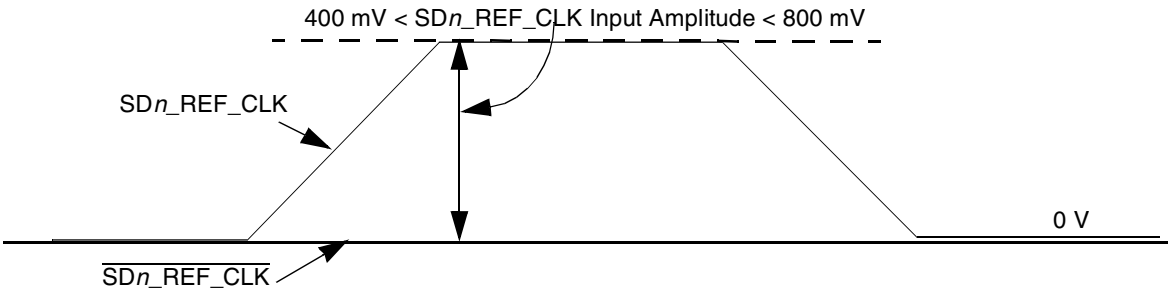

Figure 55. Single-Ended Reference Clock Input DC Requirements

21.2.3 Interfacing With Other Differential Signaling Levels

The following list provides information about interfacing with other differential signaling levels.

- With on-chip termination to SGND_SRDS*n* (xcorevss), the differential reference clocks inputs are HCSL (high-speed current steering logic) compatible DC-coupled.
- Many other low voltage differential type outputs like LVDS (low voltage differential signaling) can be used but may need to be AC-coupled due to the limited common mode input range allowed (100 mV to 400 mV) for DC-coupled connection.
- LVPECL outputs can produce signal with too large amplitude and may need to be DC-biased at clock driver output first, then followed with series attenuation resistor to reduce the amplitude, in addition to AC-coupling.

21.3 SerDes Transmitter and Receiver Reference Circuits

This figure shows the reference circuits for SerDes data lane's transmitter and receiver.

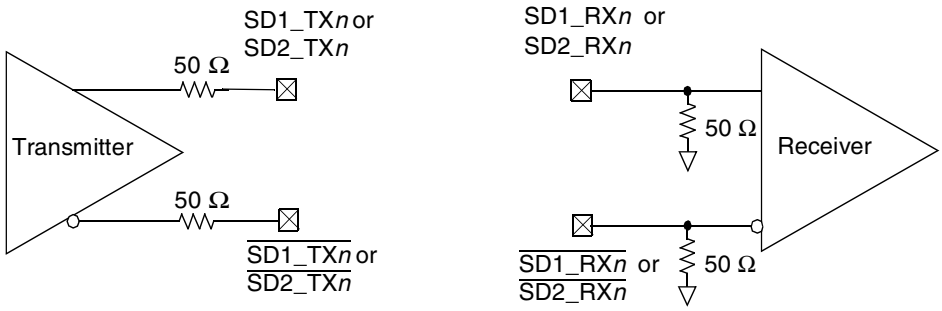

Figure 62. SerDes Transmitter and Receiver Reference Circuits

The DC and AC specification of SerDes data lanes are defined in each interface protocol section below in this document based on the application usage:

- Section 8, "Ethernet: Enhanced Three-Speed Ethernet (eTSEC)"
- Section 15, "PCI Express"
- Section 16, "Serial ATA (SATA)"

Note that an external AC coupling capacitor is required for the above three serial transmission protocols with the capacitor value defined in specification of each protocol section.

22 Package and Pin Listings

This section details package parameters, pin assignments, and dimensions.

22.1 Package Parameters for the MPC8377E TePBGA II

The package parameters are provided in the following list. The package type is 31 mm × 31 mm, 689 plastic ball grid array (TePBGA II).

Package outline	31 mm × 31 mm
Interconnects	689
Pitch	1.00 mm
Module height (typical)	2.0 mm to 2.46 mm (maximum)
Solder Balls	3.5% Ag, 96.5% Sn
Ball diameter (typical)	0.60 mm

Table 72. TePBGA II Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Note
UART_RTS_B[2]	L29	O	OVDD	—
Enhanced Local Bus Controller (eLBC) Interface				
LAD0	E24	I/O	LBVDD	—
LAD1	G28	I/O	LBVDD	—
LAD2	H25	I/O	LBVDD	—
LAD3	F26	I/O	LBVDD	—
LAD4	C26	I/O	LBVDD	—
LAD5	J28	I/O	LBVDD	—
LAD6	F21	I/O	LBVDD	—
LAD7	F23	I/O	LBVDD	—
LAD8	E25	I/O	LBVDD	—
LAD9	E26	I/O	LBVDD	—
LAD10	A23	I/O	LBVDD	—
LAD11	F24	I/O	LBVDD	—
LAD12	G24	I/O	LBVDD	—
LAD13	F25	I/O	LBVDD	—
LAD14	H28	I/O	LBVDD	—
LAD15	G25	I/O	LBVDD	—
LA11/LAD16	F27	I/O	LBVDD	—
LA12/LAD17	B21	I/O	LBVDD	—
LA13/LAD18	A25	I/O	LBVDD	—
LA14/LAD19	C28	I/O	LBVDD	—
LA15/LAD20	H24	I/O	LBVDD	—
LA16/LAD21	E23	I/O	LBVDD	—
LA17/LAD22	B28	I/O	LBVDD	—
LA18/LAD23	D28	I/O	LBVDD	—
LA19/LAD24	A27	I/O	LBVDD	—
LA20/LAD25	C25	I/O	LBVDD	—
LA21/LAD26	B27	I/O	LBVDD	—
LA22/LAD27	H27	I/O	LBVDD	—
LA23/LAD28	E21	I/O	LBVDD	—
LA24/LAD29	F20	I/O	LBVDD	—

Table 72. TePBGA II Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Note
PCI_AD27	AA29	I/O	OVDD	—
PCI_AD28	AC24	I/O	OVDD	—
PCI_AD29	AC25	I/O	OVDD	—
PCI_AD30	AB28	I/O	OVDD	—
PCI_AD31	AE24	I/O	OVDD	—
PCI_C_BE_B0	T26	I/O	OVDD	—
PCI_C_BE_B1	T28	I/O	OVDD	—
PCI_C_BE_B2	V29	I/O	OVDD	—
PCI_C_BE_B3	Y29	I/O	OVDD	—
PCI_DEVSEL_B	U28	I/O	OVDD	5
PCI_FRAME_B	V27	I/O	OVDD	—
PCI_GNT_B0	AE27	I/O	OVDD	—
PCI_GNT_B[1]/ CPCI_HS_LED	AC28	O	OVDD	—
PCI_GNT_B[2]/ CPCI_HS_ENUM	AD27	O	OVDD	—
PCI_GNT_B[3]/PCI_PME	AC27	O	OVDD	—
PCI_GNT_B[4]	AE25	O	OVDD	—
PCI_IDSEL	W28	I	OVDD	5
PCI_INTA_B/IRQ_OUT_B	AD29	O	OVDD	2
PCI_IRDY_B	U29	I/O	OVDD	5
PCI_PAR	V25	I/O	OVDD	—
PCI_PERR_B	Y25	I/O	OVDD	5
PCI_REQ_B0	AE26	I/O	OVDD	—
PCI_REQ_B[1]/CPCI_HS_ES	AC29	I	OVDD	—
PCI_REQ_B2	AB29	I	OVDD	—
PCI_REQ_B3	AD26	I	OVDD	—
PCI_REQ_B4	W27	I	OVDD	—
PCI_RESET_OUT_B	AD28	O	OVDD	—
PCI_SERR_B	V26	I/O	OVDD	5
PCI_STOP_B	W26	I/O	OVDD	5
PCI_TRDY_B	Y24	I/O	OVDD	5
M66EN	AD15	I	OVDD	—

Table 72. TePBGA II Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Note
Programmable Interrupt Controller (PIC) Interface				
MCP_OUT_B	AD14	O	OVDD	2
IRQ_B0/MCP_IN_B/GPIO2[12]	F9	I/O	OVDD	—
IRQ_B1/GPIO2[13]	E9	I/O	OVDD	—
IRQ_B2/GPIO2[14]	F10	I/O	OVDD	—
IRQ_B3/GPIO2[15]	D9	I/O	OVDD	—
IRQ_B4/GPIO2[16]/SD_WP	C9	I/O	OVDD	—
IRQ_B5/GPIO2[17]/ USBDR_PWRFAULT	AE10	I/O	OVDD	—
IRQ_B6/GPIO2[18]	AD10	I/O	OVDD	—
IRQ_B7/GPIO2[19]	AD9	I/O	OVDD	—
PMC Interface				
QUIESCE_B	D13	O	OVDD	—
SerDes1 Interface				
L1_SD_IMP_CAL_RX	AJ14	I	L1_XPADVDD	—
L1_SD_IMP_CAL_TX	AG19	I	L1_XPADVDD	—
L1_SD_REF_CLK	AJ17	I	L1_XPADVDD	—
L1_SD_REF_CLK_B	AH17	I	L1_XPADVDD	—
L1_SD_RXA_N	AJ15	I	L1_XPADVDD	—
L1_SD_RXA_P	AH15	I	L1_XPADVDD	—
L1_SD_RXE_N	AJ19	I	L1_XPADVDD	—
L1_SD_RXE_P	AH19	I	L1_XPADVDD	—
L1_SD_TXA_N	AF15	O	L1_XPADVDD	—
L1_SD_TXA_P	AE15	O	L1_XPADVDD	—
L1_SD_TXE_N	AF18	O	L1_XPADVDD	—
L1_SD_TXE_P	AE18	O	L1_XPADVDD	—
L1_SDAVDD_0	AJ18	SerDes PLL Power (1.0 or 1.05 V)	—	—
L1_SDAVSS_0	AG17	SerDes PLL GND	—	—
L1_XCOREVDD	AH14, AJ16, AF17, AH20, AJ20	SerDes Core Power (1.0 or 1.05 V)	—	—

Table 72. TePBGA II Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Note
SPIMISO/SD_DAT0	AD11	I/O	OVDD	—
SPIMOSI/SD_CMD	AJ9	I/O	OVDD	—
SPISEL_B/SD_CD	AE11	I	OVDD	—
System Control Interface				
SRESET_B	AD12	I/O	OVDD	2
HRESET_B	AE12	I/O	OVDD	1
PORESET_B	AE14	I	OVDD	—
Test Interface				
TEST	E10	I	OVDD	10
TEST_SEL0	D10	I	OVDD	13
TEST_SEL1	D12	I	OVDD	13
Thermal Management				
Reserved	F15	I	—	14
Power Supply Signals				
LVDD1	AC21, AG21, AH23	Power for eTSEC 1 I/O (2.5 V, 3.3 V)	LVDD1	—
LVDD2	AG24, AH27, AH29	Power for eTSEC 2 I/O (2.5 V, 3.3 V)	LVDD2	—
LBVDD	G20, D22, A24, G26, D27, A28	Power for eLBC (3.3, 2.5, or 1.8 V)	LBVDD	—
VDD	K10, L10, M10, N10, P10, R10, T10, U10, V10, W10, Y10, K11, R11, Y11, K12, Y12, K13, Y13, K14, Y14, K15, L15, W15, Y15, K16, Y16, K17, Y17, K18, Y18, K19, R19, Y19, K20, L20, M20, N20, P20, R20, T20, U20, V20, W20, Y20	Power for Core (1.0 V or 1.5 V)	VDD	—

Table 73. Configurable Clock Units (continued)

Unit	Default Frequency	Options
PCI Express1, 2	csb_clk/3	Off, c*sb_clk, csb_clk/2, csb_clk/3*
SATA1, 2	csb_clk/3	Off, *csb_clk*

1 This only applies to I^2C1 (I^2C2 clock is not configurable).

This table provides the operating frequencies for the TePBGA II package under recommended operating conditions (see Table 3).

Table 74. Operating Frequencies for TePBGA II

Parameter[1]	Minimum Operating Frequency (MHz)	Maximum Operating Frequency (MHz)
e300 core frequency (*core_clk*)	333	800
Coherent system bus frequency (*csb_clk*)	133	400
DDR2 memory bus frequency (MCK)[1]	250	400
DDR1 memory bus frequency (MCK) [2]	167	333
Local bus frequency (LCLK*n*)[1]	—	133
Local bus controller frequency (*lbc_clk*)	—	400
PCI input frequency (CLKIN or PCI_CLK)	25	66
eTSEC frequency	133	400
Security encryption controller frequency	—	200
USB controller frequency	—	200
eSDHC controller frequency	—	200
PCI Express controller frequency	—	400
SATA controller frequency	—	200

Notes:
1. The CLKIN frequency, RCWLR[SPMF], and RCWLR[COREPLL] settings must be chosen such that the resulting *csb_clk*, MCK, LCLK[0:2], and *core_clk* frequencies do not exceed their respective maximum or minimum operating frequencies. The value of SCCR[xCM] must be programmed such that the maximum internal operating frequency of the Security core, USB modules, SATA, and eSDHC will not exceed their respective value listed in this table.
2. The DDR data rate is 2× the DDR memory bus frequency.
3. The local bus frequency is ½, ¼, or 1/8 of the *lbiu_clk* frequency (depending on LCRR[CLKDIV]) which is in turn 1× or 2× the *csb_clk* frequency (depending on RCWLR[LBCM]).

Table 79. e300 Core PLL Configuration (continued)

RCWLR[COREPLL]			*core_clk* : *csb_clk* Ratio	VCO Divider [1]
0–1	2–5	6		
01	**0001**	1	1.5:1	4
10	**0001**	1	1.5:1	8
00	**0010**	0	2:1	2
01	**0010**	0	2:1	4
10	**0010**	0	2:1	8
00	**0010**	1	2.5:1	2
01	**0010**	1	2.5:1	4
10	**0010**	1	2.5:1	8
00	**0011**	0	3:1	2
01	**0011**	0	3:1	4
10	**0011**	0	3:1	8
00	**0011**	1	3.5:1	2
01	**0011**	1	3.5:1	4
10	**0011**	1	3.5:1	8
00	**0100**	0	4:1	2
01	**0100**	0	4:1	4
10	**0100**	0	4:1	8

Notes:
1. Core VCO frequency = Core frequency × VCO divider. Note that VCO divider has to be set properly so that the core VCO frequency is in the range of 800–1600 MHz.

23.3 Suggested PLL Configurations

This table shows suggested PLL configurations for different input clocks (LBCM = 0).

Table 80. Example Clock Frequency Combinations

								eLBC [1]			e300 Core [1]				
Ref [1]	**LBCM**	**DDRCM**	**SVCOD**	**SPMF**	**Sys VCO[1,2]**	**CSB[1,3]**	**DDR data rate[1,4]**	**/2**	**/4**	**/8**	**× 1**	**× 1.5**	**× 2**	**× 2.5**	**× 3**
25.0	0	1	2	5	500	125	250	62.5	31.3	15.6	—	—	—	—	375
25.0	0	1	2	6	600	150	300	75 [6]	37.5	18.8	—	—	—	375	450
33.3	0	1	2	5	667	167	333	83.3 [6]	41.6	20.8	—	—	333	416	500
33.3	0	1	2	4	533	133	267	66.7	33.3	16.7	—	—	—	333	400

Tyco Electronics
Chip Coolers™
www.chipcoolers.com

Wakefield Engineering
www.wakefield.com

Interface material vendors include the following:

Chomerics, Inc.
www.chomerics.com

Dow-Corning Corporation
Dow-Corning Electronic Materials
www.dowcorning.com

Shin-Etsu MicroSi, Inc.
www.microsi.com

The Bergquist Company
www.bergquistcompany.com

24.3 Heat Sink Attachment

The device requires the use of heat sinks. When heat sinks are attached, an interface material is required, preferably thermal grease and a spring clip. The spring clip should connect to the printed circuit board, either to the board itself, to hooks soldered to the board, or to a plastic stiffener. Avoid attachment forces that can lift the edge of the package or peel the package from the board. Such peeling forces reduce the solder joint lifetime of the package. The recommended maximum compressive force on the top of the package is 10 lb force (4.5 kg force). Any adhesive attachment should attach to painted or plastic surfaces, and its performance should be verified under the application requirements.

24.3.1 Experimental Determination of the Junction Temperature with a Heat Sink

When a heat sink is used, the junction temperature is determined from a thermocouple inserted at the interface between the case of the package and the interface material. A clearance slot or hole is normally required in the heat sink. Minimize the size of the clearance to minimize the change in thermal performance caused by removing part of the thermal interface to the heat sink. Because of the experimental difficulties with this technique, many engineers measure the heat sink temperature and then back calculate the case temperature using a separate measurement of the thermal resistance of the interface. From this case temperature, the junction temperature is determined from the junction to case thermal resistance.

$$T_J = T_C + (R_{\theta JC} \times P_D)$$

where:

T_J = junction temperature (°C)

T_C = case temperature of the package (°C)